September 2010



FAN5353 3MHz, 3A Synchronous Buck Regulator

Features

- 3MHz Fixed-Frequency Operation
- Best-in-Class Load Transient
- 3A Output Current Capability
- 2.7V to 5.5V Input Voltage Range
- Adjustable Output Voltage: 0.8V to V_{IN}•0.9
- Power Good Output
- Internal Soft-Start
- Input Under-Voltage Lockout (UVLO)
- Thermal Shutdown and Overload Protection
- 12-lead 3x3.5mm MLP

Applications

- Set-Top Box
- Hard Disk Drive
- Communications Cards
- DSP Power

Description

The FAN5353 is a step-down switching voltage regulator that delivers an adjustable output from an input voltage supply of 2.7V to 5.5V. Using a proprietary architecture with synchronous rectification, the FAN5353 is capable of delivering 3A at over 85% efficiency. The regulator operates at a nominal fixed frequency of 3MHz, which reduces the value of the external components to 470nH for the output inductor and 10µF for the output capacitor. Additional output capacitance can be added without affecting stability if tighter regulation during transients is required. The regulator includes an open-drain power good (PGOOD) signal that pulls low when the output is not in regulation.

In shutdown mode, the supply current drops below 1 μ A, reducing power consumption.

FAN5353 is available in a 12-lead 3x3.5mm MLP package.

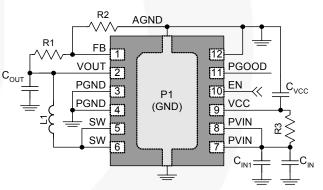


Figure 1. Typical Application

Ordering Information

Part Number	Temp. Range	Package	Packing Method
FAN5353MPX	-40 to 85°C	MLP-12, 3x3.5mm	Tape and Reel

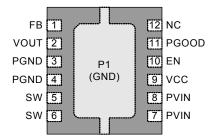
Component	Description	Vendor	Parameter	Тур.	Units
		Vishay IHLP1616ABER47M01	L	0.47	μH
L1	470nH nominal	CoiltronicsSD12-R47-R TDK VLC5020T-R47N MURATA LQH55PNR47NT0	DCR	20	mΩ
C _{OUT}	2 pieces 10μF, 6.3V, X5R, 0805	GRM21BR60J106M (Murata)	С	10.0	μF
C _{IN}	10μF, 6.3V, X5R, 0805	C2012X5R0J106M (TDK)			
C _{IN1}	10nF, 25V, X7R, 0402	GRM155R71E103K (Murata) C1005X7R1E103K (TDK)	С	10	nF
C _{VCC}	4.7μF, 6.3V, X5R, 0603	GRM188R60J475K (Murata) C1608X5R0J475K (TDK)	С	4.7	μF
R3 ⁽¹⁾	Resistor: 1Ω 0402	any	R	1	Ω

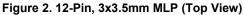
Table 1. Recommended External Components for 3A Maximum Load Current

Note:

1. R3 is optional and improves IC power supply noise rejection. See Layout recommendations for more information.

Pin Configuration





Pin Definitions

Pin #	Name	Description
1	FB	FB. Connect to resistor divider. The IC regulates this pin to 0.8V.
2	VOUT	VOUT. Sense pin for VOUT. Connect to COUT.
3, 4	PGND	Power Ground . Low-side MOSFET is referenced to this pin. CIN and COUT should be returned with a minimal path to these pins.
5, 6	SW	Switching Node. Connect to inductor.
P1	GND	Ground. All signals are referenced to this pin.
7, 8	PVIN	Power Input Voltage. Connect to input power source. Connect to CIN with minimal path.
9	VCC	IC Bias Supply . Connect to input power source. Use a separate bypass capacitor CVCC from this pin to the P1 GND terminal between pins 1 and 12.
10	EN	Enable. The device is in shutdown mode when this pin is LOW. Do not leave this pin floating.
11	PGOOD	Power Good. This open-drain pin pulls LOW if the output falls out of regulation or is in soft-start.
12	NC	This pin has no function and should be tied to GND.
	l	

Note:

2. P1 is the bottom heat-sink pad. Ground plane should flow through pins 3, 4, 12, and P1 and can be extended through pin 11 if PGOOD's function is not required to improve IC cooling.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Parameter		Min.	Max.	Units
	IC Not Switching	-0.3	7.0	V
SVV, PVIIN, VCC PIIIS	IC Switching	-0.3	6.5	v
Other Pins		-0.3	V_{CC} + 0.3 ⁽³⁾	V
Maximum Slew Rate of VIN Abc	Aximum Slew Rate of VIN Above 6.5V when PWM is Switching		15	V/ms
Pull-Up Resistance from PGOO	D to VCC	1		KΩ
Electrostatic Discharge	Human Body Model per JESD22-A114		2	KV
Protection Level	Charged Device Model per JESD22-C101	2		KV
Junction Temperature		-40	+150	°C
Storage Temperature		-65	+150	°C
_ead Soldering Temperature, 10 Seconds			+260	°C
	SW, PVIN, VCC Pins Other Pins Maximum Slew Rate of VIN Abo Pull-Up Resistance from PGOO Electrostatic Discharge Protection Level Junction Temperature Storage Temperature	SW, PVIN, VCC Pins IC Not Switching IC Switching IC Switching Other Pins Maximum Slew Rate of VIN Above 6.5V when PWM is Switching Pull-Up Resistance from PGOOD to VCC Electrostatic Discharge Protection Level Human Body Model per JESD22-A114 Charged Device Model per JESD22-C101 Junction Temperature	SW, PVIN, VCC Pins IC Not Switching -0.3 IC Switching -0.3 Other Pins -0.3 Maximum Slew Rate of VIN Above 6.5V when PWM is Switching -0.3 Pull-Up Resistance from PGOOD to VCC 1 Electrostatic Discharge Protection Level Human Body Model per JESD22-A114 Junction Temperature -40 Storage Temperature -65	In the initial sector of the initial

Note:

3. Lesser of 7V or V_{CC} +0.3V.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Тур.	Max.	Units
V _{CC} , V _{IN}	Supply Voltage Range	2.7		5.5	V
V _{OUT}	Output Voltage Range	0.8		90% Duty Cycle	V
I _{OUT}	Output Current	0		3	А
L	Inductor		0.47		μH
CIN	Input Capacitor		10		μF
C _{OUT}	Output Capacitor		20		μF
TA	Operating Ambient Temperature	-40		+85	°C
TJ	Operating Junction Temperature	-40		+125	°C

Thermal Properties

Symbol	Parameter	Min.	Тур.	Max.	Units
θ_{JA}	Junction-to-Ambient Thermal Resistance ⁽⁴⁾		46		°C/W

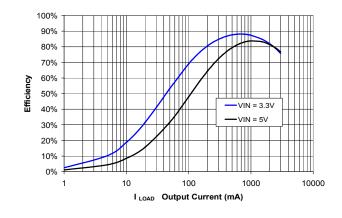
Note:

 Junction-to-ambient thermal resistance is a function of application and board layout. This data is measured with four-layer 1s2p boards in accordance to JESD51- JEDEC standard. Special attention must be paid not to exceed junction temperature T_{J(max)} at a given ambient temperate T_A.

Electrical Characteristics

Minimum and maximum values are at V_{IN} = 2.7V to 5.5V, $T_A = -40^{\circ}C$ to +85°C, unless otherwise noted. Typical values are at $T_A = 25^{\circ}C$, $V_{IN} = 5V$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Power Su	oplies			1		
lq	Quiescent Current	$I_{LOAD} = 0, V_{OUT} = 1.2V$		14		mA
I _{SD}	Shutdown Supply Current	EN = GND		0.1	3.0	μA
		V _{IN} Rising		2.83	2.95	V
V _{UVLO}	Under-Voltage Lockout Threshold	V _{IN} Falling	2.10	2.30	2.40	V
VUVHYST	Under-Voltage Lockout Hysteresis			530		mV
Logic Pins	5					
VIH	HIGH-Level Input Voltage		1.05			V
VIL	LOW-Level Input Voltage				0.4	V
V_{LHYST}	Logic Input Hysteresis Voltage			100		mV
I _{IN}	Input Bias Current	Input tied to GND or V_{IN}		0.01	1.00	μA
I _{OUTL}	PGOOD Pull-Down Current	V _{PGOOD} = 0.4V			1	mA
IOUTH	PGOOD HIGH Leakage Current	V _{PGOOD} = V _{IN}		0.01	1	μA
VOUT Reg	ulation	· · ·				
N/	Output Reference DC Accuracy	T _A = 25°C	0.792	0.800	0.808	V
V_{REF}	Measured at FB Pin		0.788	0.800	0.812	V
V_{REG}	V _{OUT} DC Accuracy	At VOUT pin W.R.T. Calculated Value, I _{LOAD} = 500mA	1.6%		+1.6	%
$\frac{\Delta V_{OUT}}{\Delta I_{LOAD}}$	Load Regulation	$I_{OUT(DC)} = 0$ to 3A		-0.03		%/A
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	$2.7V \le V_{IN} \le 5.5V, I_{OUT(DC)} = 1.5A$		0.01		%/V
	Transient Response	I_{LOAD} step 0.1A to 1.5A, $t_r = t_f =$ 100ns, $V_{OUT}=1.2V$		<u>+</u> 20		mV
Power Sw	itch and Protection	· · ·				
R _{DS(ON)P}	P-channel MOSFET On Resistance			60		mΩ
R _{DS(ON)N}	N-channel MOSFET On Resistance			40		mΩ
I _{LIMPK}	P-MOS Peak Current Limit		3.75	4.55	5.50	А
TLIMIT	Thermal Shutdown			150		°C
T _{HYST}	Thermal Shutdown Hysteresis			20		°C
N/	Input OVP Shutdown	Rising Threshold		6.2		V
V _{SDWN}		Falling Threshold	5.50	5.85		V
Frequency	/ Control					
f _{SW}	Oscillator Frequency		2.7	3.0	3.3	MHz
Soft-Start						
		$R_{LOAD} \ge 5\Omega$, to $V_{OUT} = 1.2V$		210	250	μs
t _{ss}	Regulator Enable to Regulated V_{OUT}	$R_{LOAD} \ge 5\Omega$, to $V_{OUT} = 1.8V$		340	420	μS
VSLEW	Soft-Start VOUT Slew Rate			10	1	V/ms



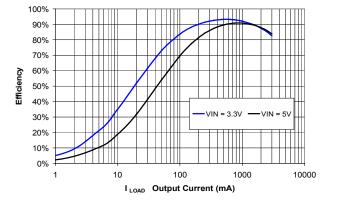


Figure 3. Efficiency vs. ILOAD at VOUT = 1.2V

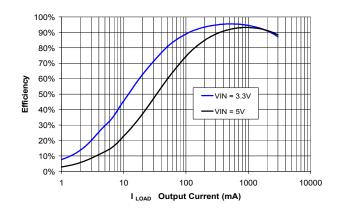


Figure 5. Efficiency vs. ILOAD at VOUT = 2.5V

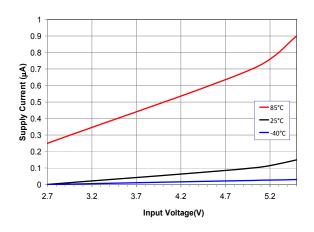


Figure 7. Shutdown Supply Current vs. V_{IN}, EN to 0V

Figure 4. Efficiency vs. ILOAD at VOUT = 1.8V

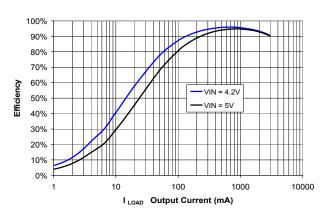


Figure 6. Efficiency vs. ILOAD at VOUT = 3.3V

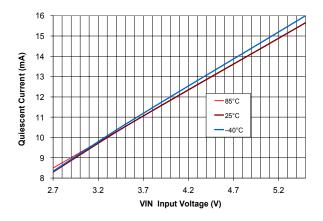


Figure 8. Quiescent Current vs. V_{IN}, No Load

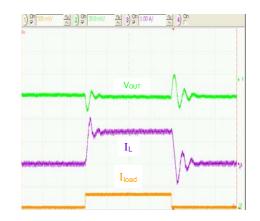


Figure 9. Load Transient Response: 100mA to 1.5A to 100mA, $t_r=t_f=100$ ns, Horizontal Scale = 5µs/div.

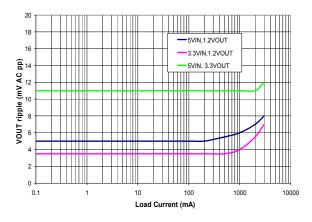


Figure 11. Output Voltage Ripple vs. Load Current

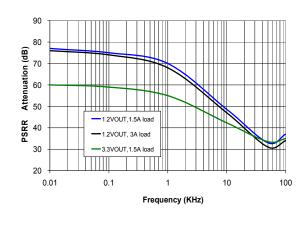


Figure 13. Power Supply Rejection Ratio

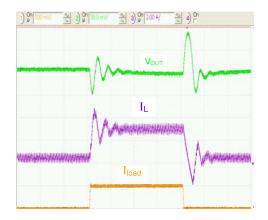
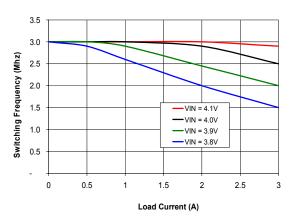
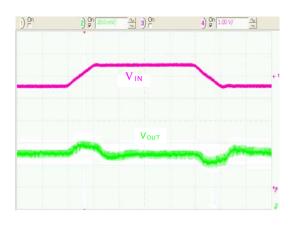


Figure 10. Load Transient Response: 500mA to 3A to 500mA, t_r=t_f=100ns, Horizontal Scale = 5µs/div.









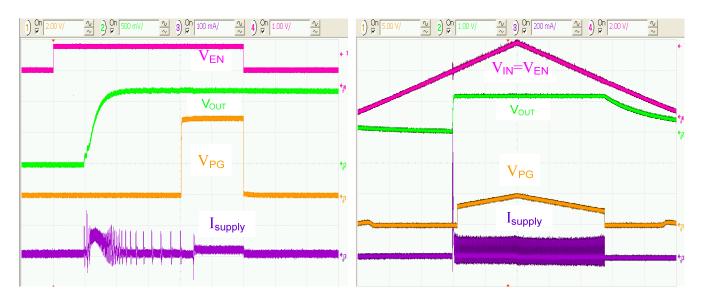


Figure 15. Soft-Start: EN Voltage Raised After V_{IN} =5.0V, I_{LOAD} = 0, Horizontal Scale = 100µs/div.





Figure 16. Soft-Start: EN Pin Tied to VCC, $I_{LOAD} = 0$, Horizontal Scale = 1ms/div.



Figure 18. Soft-Start: EN Pin Tied to VCC, R_{LOAD} = 400m Ω , C_{OUT} = 100 μ F, Horizontal Scale = 1ms/div.

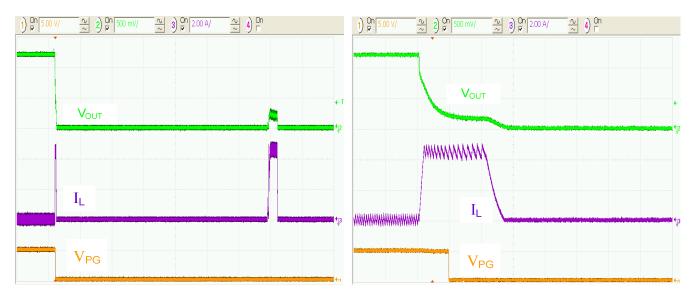


Figure 19. VOUT to GND Short Circuit, 200µs/div.

Figure 20. VOUT to GND Short Circuit, 5µs/div.

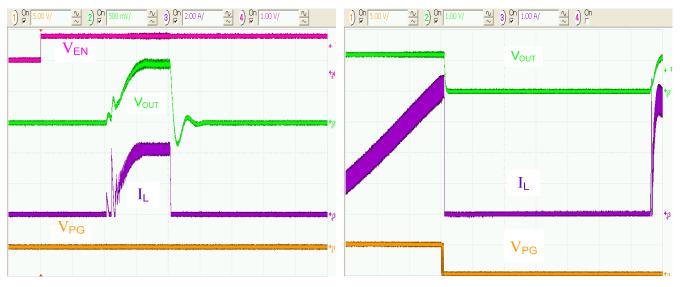


Figure 21. Over-Current at Startup: $R_{LOAD} = 200m\Omega$., 50µs/div.



Operation Description

The FAN5353 is a step-down switching voltage regulator that delivers an adjustable output from an input voltage supply of 2.7V to 5.5V. Using a proprietary architecture with synchronous rectification, the FAN5353 is capable of delivering 3A at over 80% efficiency. The regulator operates at a nominal frequency of 3MHz at full load, which reduces the value of the external components to 470nH for the output inductor and 20µF for the output capacitor.

Control Scheme

The FAN5353 uses a proprietary non-linear, fixed-frequency PWM modulator to deliver a fast load transient response, while maintaining a constant switching frequency over a wide range of operating conditions. The regulator performance is independent of the output capacitor ESR, allowing for the use of ceramic output capacitors. Although this type of operation normally results in a switching frequency that varies with input voltage and load current, an internal frequency loop holds the switching frequency constant over a large range of input voltages and load currents.

Setting the Output Voltage

The output voltage is set by the R1, R2, and V_{REF} (0.8V):

$$\frac{R1}{R2} = \frac{V_{OUT} - V_{REF}}{V_{REF}}$$
(1)

R1 must be set at or below 100K Ω . Therefore:

$$R2 = \frac{R1 \cdot 0.8}{(V_{OUT} - 0.8)}$$
(2)

For example, for V_{OUT} = 1.2V, R1 = 100K Ω , R2 = 200K Ω .

Enable and Soft Start

When the EN pin is LOW, the IC is shut down, all internal circuits are off, and the part draws very little current. Raising EN above its threshold voltage activates the part and starts the soft-start cycle. During soft-start, the modulator's internal reference is ramped slowly to minimize any large surge currents on the input and prevents any overshoot of the output voltage.

If large values of output capacitance are used, the regulator may fail to start. If V_{OUT} fails to achieve regulation within 320µs from the beginning of soft-start, the regulator shuts down and waits 1200µs before attempting a restart. If the regulator is at its current limit for more than about 60µs, the regulator shuts down before restarting 1200µs later. This limits the C_{OUT} capacitance when a heavy load is applied during the startup. For a typical FAN5353 starting with a resistive load:

$$COUT_{MAX}(\mu F) \approx 400 - 100 * I_{LOAD}(A)$$

where $I_{LOAD} = \frac{V_{OUT}}{R_{LOAD}}$ (3)

Synchronous rectification is inhibited during soft-start, allowing the IC to start into a pre-charged load.

PGOOD Pin

The PGOOD pin is an open drain output that indicates the IC is in regulation when its state is open. PGOOD requires an external pull-up resistor. PGOOD pulls LOW under the following conditions:

- 1. The IC has operated in cycle-by-cycle current limit for eight or more consecutive PWM cycles.
- 2. The circuit is disabled; either after a fault occurs, or when EN is LOW.
- 3. The IC is performing a soft-start.

Under-Voltage Lockout

When EN is HIGH, the under-voltage lockout keeps the part from operating until the input supply voltage rises high enough to properly operate. This ensures no misbehavior of the regulator during startup or shutdown.

Input Over-Voltage Protection (OVP)

When V_{IN} exceeds V_{SDWN} (about 6.2V) the IC stops switching, to protect the circuitry from internal spikes above 6.5V. An internal 40µs filter prevents the circuit from shutting down due to noise spikes. For the circuit to fully protect the internal circuitry, the V_{IN} slew rate above 6.2V must be limited to no more than 15V/ms when the IC is switching.

The IC protects itself if V_{IN} overshoots to 7V during initial power-up as long as the V_{IN} transition from 0 to 7V occurs in less than $10\mu s$ (10% to 90%).

Current Limiting

A heavy load or short circuit on the output causes the current in the inductor to increase until a maximum current threshold is reached in the high-side switch. Upon reaching this point, the high-side switch turns off, preventing high currents from causing damage. 16 consecutive PWM cycles in current limit cause the regulator to shut down and stay off for about 1200 μ s before attempting a restart.

In the event of a short circuit, the soft-start circuit attempts to restart and produces an over-current fault after about $50\mu s$, which results in a duty cycle of less than 10%, providing current into a short circuit.

Thermal Shutdown

When the die temperature increases, due to a high load condition and/or a high ambient temperature, the output switching is disabled until the temperature on the die has fallen sufficiently. The junction temperature at which the thermal shutdown activates is nominally 150°C with a 20°C hysteresis.

Minimum Off-Time Effect on Switching Frequency

 $t_{ON(MIN)}$ and $t_{OFF(MIN)}$ are both 45ns. This imposes constraints on the maximum $\frac{VOUT}{VIN}$ that the FAN5353 can provide, while

still maintaining a fixed switching frequency in PWM mode. While regulation is unaffected, the switching frequency drops when the regulator cannot provide sufficient duty cycle at 3MHz to maintain regulation.

The calculation for switching frequency is given as:

$$f_{SW} = min\left(\frac{1}{t_{SW(MAX)}}, \frac{1}{333.3ns}\right)$$
(4)

where:

$$t_{SW(MAX)} = 45ns \bullet \left(1 + \frac{V_{OUT} + I_{OUT} \bullet R_{OFF}}{V_{IN} - I_{OUT} \bullet R_{ON} - V_{OUT}}\right)$$

 $R_{OFF} = R_{DSON_N} + DCR_L$

 $R_{ON} = R_{DSON_P} + DCR_L$

Applications Information

Selecting the Inductor

The output inductor must meet both the required inductance and the energy handling capability of the application. The inductor value affects the average current limit, the output voltage ripple, and the efficiency.

The ripple current (ΔI) of the regulator is:

$$\Delta I \approx \frac{V_{OUT}}{V_{IN}} \bullet \left(\frac{V_{IN} - V_{OUT}}{L \bullet f_{SW}} \right)$$
(5)

The maximum average load current, $I_{MAX(LOAD)}$ is related to the peak current limit, $I_{LIM(PK)}$ by the ripple current as:

$$I_{MAX(LOAD)} = I_{LIM(PK)} - \frac{\Delta I}{2}$$
(6)

The FAN5353 is optimized for operation with L=470nH, but is stable with inductances up to 1.2 μ H (nominal). The inductor should be rated to maintain at least 80% of its value at I_{LIM(PK)}. Failure to do so lowers the amount of DC current the IC can deliver.

Efficiency is affected by the inductor DCR and inductance value. Decreasing the inductor value for a given physical size typically decreases the DCR; but since ΔI increases, the RMS current increases, as do core and skin effect losses.

$$I_{\text{RMS}} = \sqrt{I_{\text{OUT}(\text{DC})}^2 + \frac{\Delta l^2}{12}}$$
(7)

The increased RMS current produces higher losses through the $R_{\text{DS}(\text{ON})}$ of the IC MOSFETs as well as the inductor ESR.

Increasing the inductor value produces lower RMS currents, but degrades transient response. For a given physical inductor size, increased inductance usually results in an inductor with lower saturation current. shows the effects of inductance higher or lower than the recommended 470nH on regulator performance.

Table 2. Effects of Increasing the InductorValue (from 470nH recommended value) onRegulator Performance

I _{MAX(LOAD)}	$\Delta \mathbf{V}_{OUT}$ (EQ. 8)	Transient Response		
Increase	Decrease	Degraded		

Inductor Current Rating

The FAN5353's current limit circuit can allow a peak current of 5.5A to flow through L1 under worst-case conditions. If it is possible for the load to draw that much continuous current, the inductor should be capable of sustaining that current or failing in a safe manner.

For space-constrained applications, a lower current rating for L1 can be used. The FAN5353 may still protect these inductors in the event of a short circuit, but may not be able to protect the inductor from failure if the load is able to draw higher currents than the DC rating of the inductor.

Output Capacitor

Note:

suggests 0805 capacitors, but 0603 capacitors may be used if space is at a premium. Due to voltage effects, the 0603 capacitors have a lower in-circuit capacitance than the 0805 package, which can degrade transient response and output ripple.

Increasing C_{OUT} has no effect on loop stability and can therefore be increased to reduce output voltage ripple or to improve transient response. Output voltage ripple, ΔV_{OUT} , is:

$$\Delta V_{OUT} = \Delta I \bullet \left(\frac{1}{8 \bullet C_{OUT} \bullet f_{SW}} + ESR \right)$$
(8)

where C_{OUT} is the effective output capacitance. The capacitance of C_{OUT} decreases at higher output voltages, which results in higher ΔV_{OUT} .

If C_{OUT} is greater than $100 \mu F,$ the regulator may fail to start under load.

If an inductor value greater than $1.0\mu H$ is used, at least $30\mu F$ of C_{OUT} should be used to ensure stability.

ESL Effects

The ESL (Equivalent Series Inductance) of the output capacitor network should be kept low to minimize the square wave component of output ripple that results from the division ratio C_{OUT} 's ESL and the output inductor (L_{OUT}). The square wave component due to ESL can be estimated as:

$$\Delta V_{OUT(SQ)} \approx V_{IN} \bullet \frac{ESL_{COUT}}{L1}$$
(9)

A good practice to minimize this ripple is to use multiple output capacitors to achieve the desired C_{OUT} value. For

example, to obtain C_{OUT} = 20µF, a single 22µF 0805 would produce twice the square wave ripple of 2 x 10µF 0805.

To minimize ESL, try to use capacitors with the lowest ratio of length to width. 0805s have lower ESL than 1206s. If low output ripple is a chief concern, some vendors produce 0508 or 0612 capacitors with ultra-low ESL. Placing additional small value capacitors near the load also reduces the highfrequency ripple components.

Input Capacitor

The 10 μ F ceramic input capacitor should be placed as close as possible between the VIN pin and PGND to minimize the parasitic inductance. If a long wire is used to bring power to the IC, additional "bulk" capacitance (electrolytic or tantalum) should be placed between C_{IN} and the power source lead to reduce under-damped ringing that can occur between the inductance of the power source leads and C_{IN}.

The effective C_{IN} capacitance value decreases as V_{IN} increases due to DC bias effects. This has no significant impact on regulator performance.

Layout Recommendations

The layout recommendations below highlight various topcopper planes by using different colors. It includes COUT3 to demonstrate how to add C_{OUT} capacitance to reduce ripple and transient excursions. The inductor in this example is the TDK VLC5020T-R47N.

VCC and VIN should be connected together by a thin trace some distance from the IC, or through a resistor (shown as R3 below), to isolate the switching spikes on PVIN from the IC bias supply on VCC. If PCB area is at a premium, the connection between PVIN and VCC can be made on another PCB layer through vias. The via impedance provides some filtering for the high-frequency spikes generated on PVIN.

PGND and AGND connect through the thermal pad of the IC. Extending the PGND and AGND planes improves IC cooling. The IC analog ground (AGND) is bonded to P1 between pins 1 and 12. Large AC ground currents should return to pins 3 and 4 (PGND) either through the copper under P1 between pins 6 and 7 or through a direct trace from pins 3 and 4 (as shown for COUT1-COUT3).

EN and PGOOD connect through vias to the system control logic.

CIN1 is an optional device used to provide a lower impedance path for high-frequency switching edges/spikes, which helps to reduce SW node and VIN ringing. CIN should be placed as close as possible between PGND and VIN, as shown below.

PGND connection back to inner planes should be accomplished as series of vias distributed among the COUT return track and CIN return plane between pins 6 and 7.

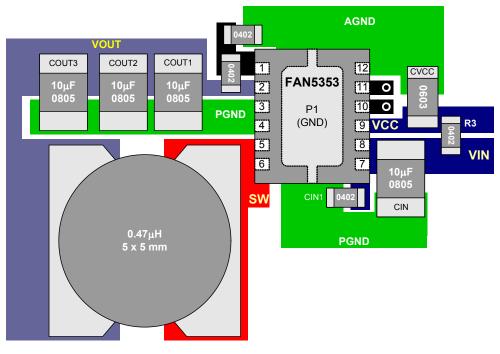
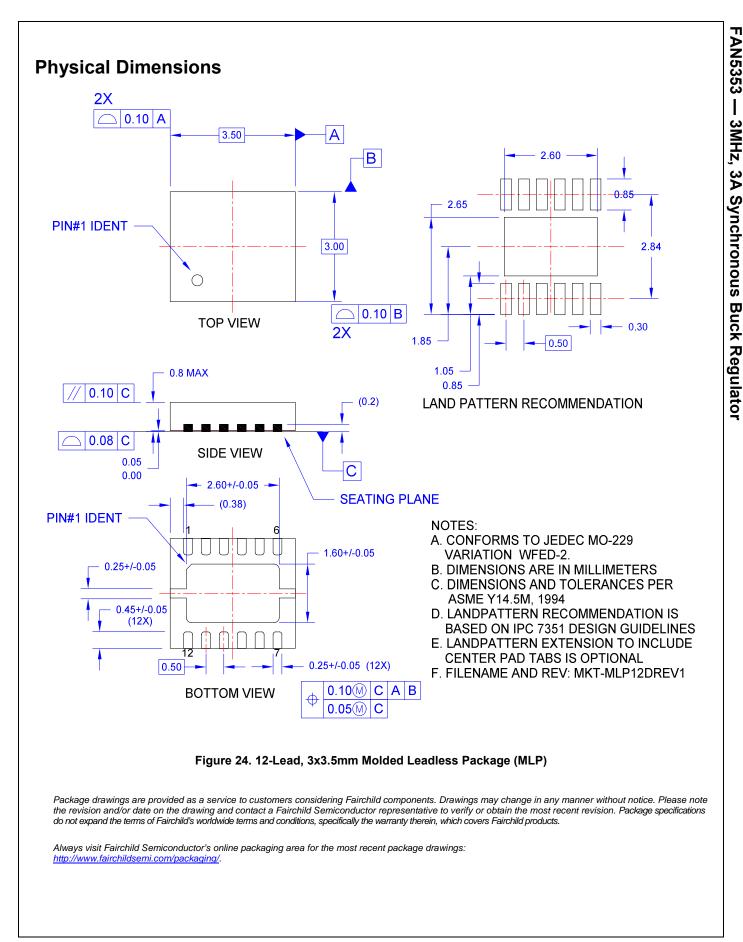


Figure 23. 3A Layout Recommendation





SEMICONDUCTOR

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